

SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 13 with:

A trend in recent years has been for CD-R/RW drives to run at increasingly higher speeds than before. That trend has entailed a growing need for semiconductor lasers ~~of producing light in~~ the 780 nm band, which are used by the high-speed drives, to provide greater output. A major constraint on getting the semiconductor laser to be more highly ~~power~~ powered is a degradation of its light emitting facet. This type of degradation, called COD (catastrophic optical damage) degradation, stems from defects in the vicinity of the light emitting facet causing optical absorption.

Replace the paragraph beginning at page 2, line 23 with:

Thereafter, ~~the back of the~~ n-GaAs substrate 102 is ~~shaved~~ reduced in thickness at the back surface to a thickness of about 100 μ m. Laser facets are ~~cleaved~~ formed by cleaving and the window layer 116 is formed by crystalline growth. The result of this process is illustrated in Fig. 15B. Forming the electrode 118 on the structure completes the semiconductor laser of Fig. 14.

Replace the paragraph beginning at page 2, line 29 with:

On the conventional semiconductor laser 100 constituted as outlined above, the window layer 116 is formed by crystalline growth on the cleaved surface following cleavage of the laser ~~facets~~ facets. This conventional process tends to be complicated because the window layer 116 and electrode 118 need to be formed after the cleaving step.

Replace the paragraph beginning at page 3, line 3 with:

Japanese Patent Publication No. 2827919, which is equivalent to U. S. Patent 4,809,289, discloses a method for forming a window structure. The method includes forming a first upper clad layer on an MQW active layer, to be topped subsequently with an ion implantation mask pattern, and forming the window structure by ~~getting~~

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~~disordering~~ the MQW active layer ~~disordered~~ in the vicinity of the laser facet by means of impurity implantation at a low energy level. According to the disclosed method, the degree of ~~the disorder~~ disordering must be controlled precisely, otherwise the window effect will not occur, resulting in a semiconductor laser degrading during use.

Replace the paragraph beginning at page 7, line 11 with:

In all figures, ~~the~~ substantially the same elements are given the same reference numbers.